

System:  
Pierre-Anne  
Bausson,  
Sébastien Dubos,  
Olivier Limousin,  
**Daniel Maier**,  
Diana Renaud,  
Paul Serrano,

ASIC:  
David Baudin,  
Olivier Gevin,  
Alicia Michalowska

Detector:  
Tadayuki Takahashi,  
Shin Watanabe



**D2R1**

the newest member in the CALISTE family

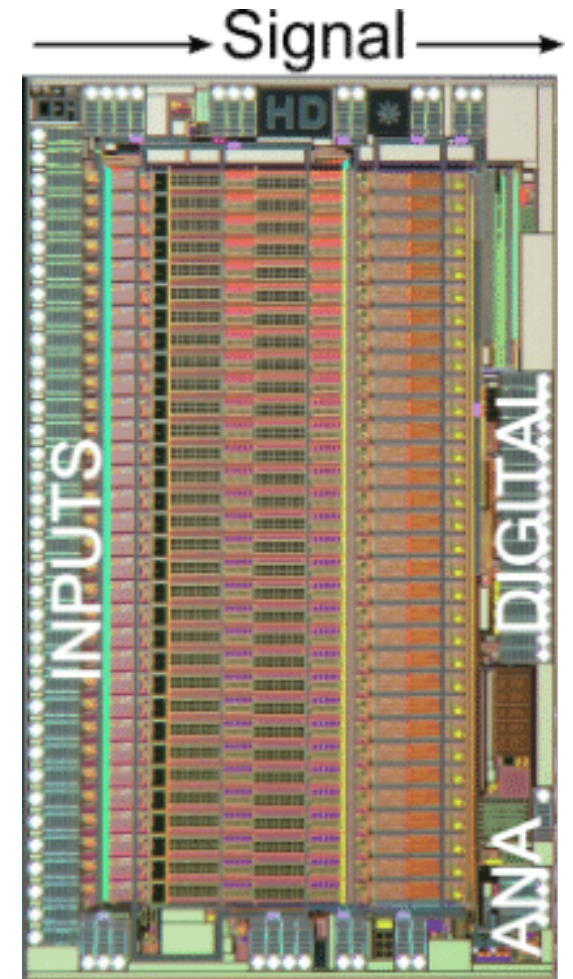


# OVERVIEW

- **review: CALISTE**
- **D2R1:**
  - design and architecture
  - first verification tests
  - next steps
- **outlook: MC2**

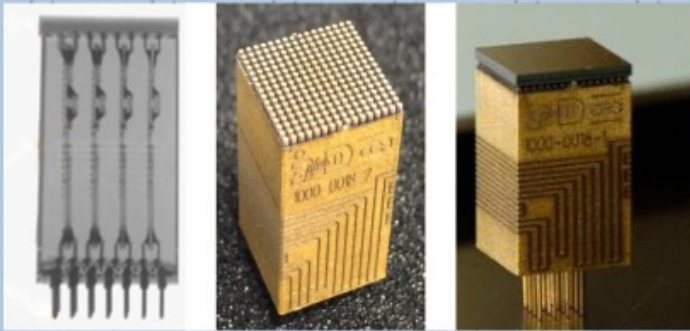
# REVIEW: CALISTE: IDeF-X

- **the Caliste detector modules are based on IDeF-X readout ASICs**
  - started in 2003; now in 7<sup>th</sup> generation
  - properties:
    - optimized for low  $C_{in}$  & low  $I_{dark}$
    - ultra-low noise,
    - low power consumption
    - channel individual triggered readout
    - designed for space applications



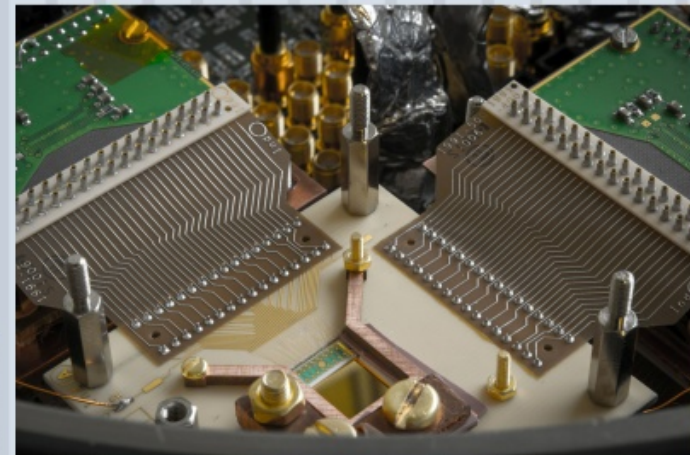
# REVIEW: applications of IDeF-X

CdTe Pixel detectors

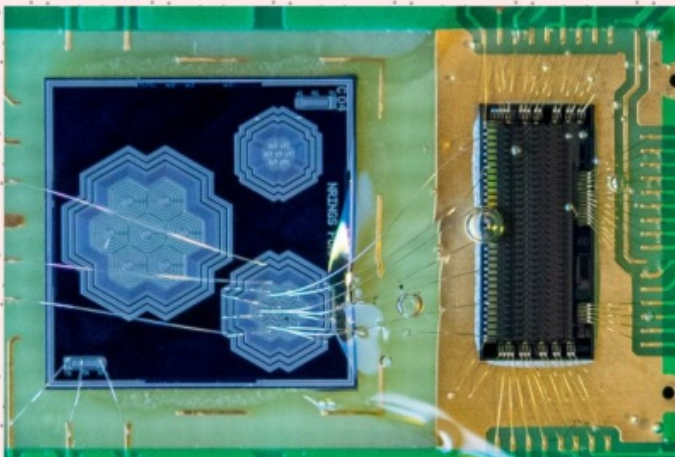


C  
A  
L  
I  
S  
T  
E

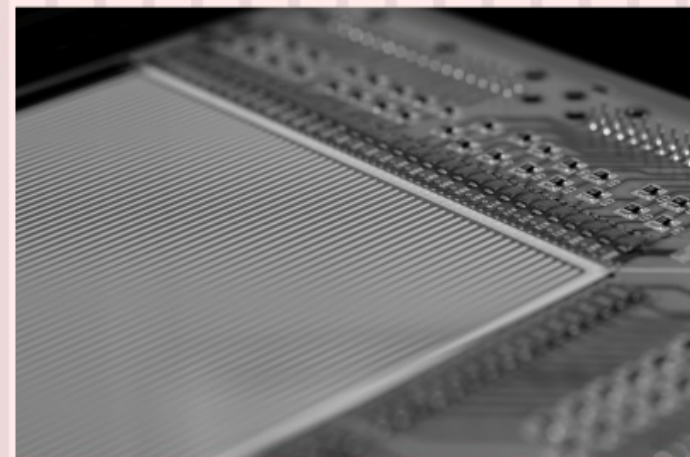
CdTe Double-sided Strip detectors



Silicon Drift detectors

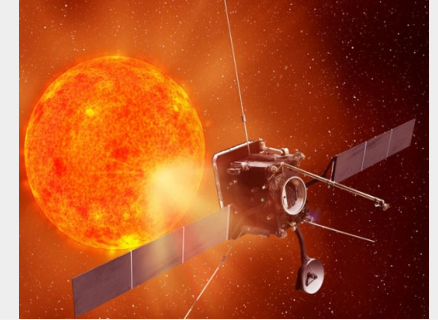
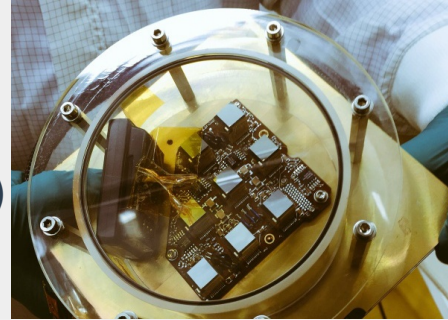


Silicon Double-sided Strip detectors

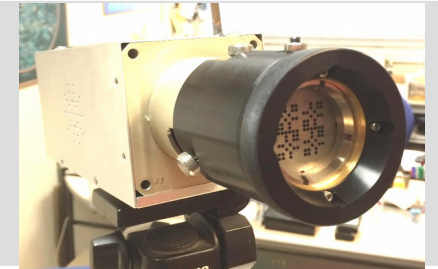
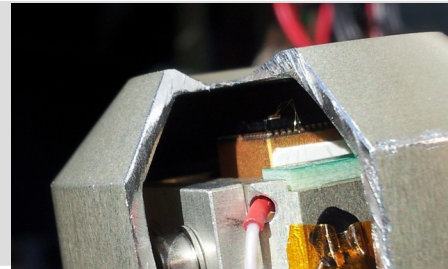


# REVIEW: applications of CALISTE

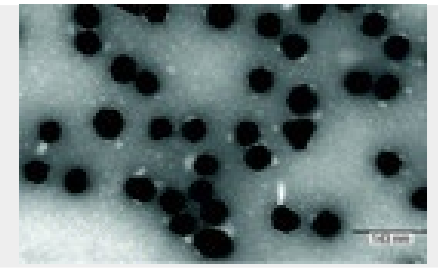
- STIX on Solar Orbiter (CALITE-SO)
  - solar mission, 2020 (ESA Cosmic Vision)



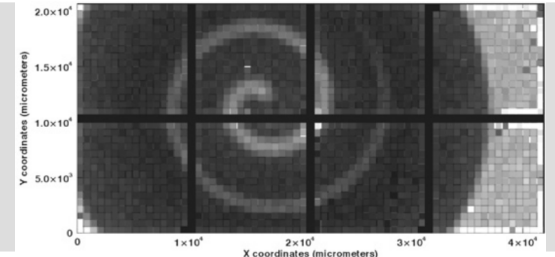
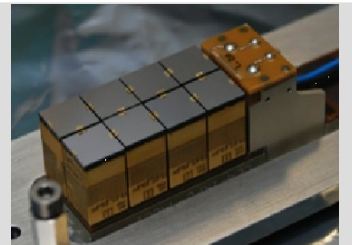
- ORIGAMIX (CALISTE-HD & -O)
  - portable gamma camera for nuclear safety



- SATBOT (CALISTE-HD)
  - assisted radiotherapy using Au-NP



- MACSI (8 x CALISTE-HD)
  - proof of concept for large focal planes
  - 4-side buttability



# REVIEW: ASIC parameters of interest

	# ch	size	technology	dynamic range	energy range	floor noise	power
	-	um <sup>2</sup>	-	fC	keV (CdTe)	e <sup>-</sup> (rms)	mW/ch
IDeF-X V1.1	16	3000 x 4000	350 nm 3.3 V	10	250	37	2.8
IDeF-X V2	32	2800 x 6400	350 nm 3.3 V	8	200	33	3.0
IDeF-X HD	32	3500 x 5900	350 nm 3.3 V	10-40	250-1000	31	0.8
D2R1	?	?	?	?	?	?	?

# REVIEW: ASIC parameters of interest

- **What do we want to achieve?**
  - **Which parameters need modification?**
  - **How to do it?**
- a look on the detector characteristics might help...**

# REVIEW: detector parameters of interest

	ASIC	# pix	pixel pitch	detector area	thickness	spectr. res	power
			um	mm <sup>2</sup>	mm	eV (FWHM @ 60 keV)	mW/mm <sup>2</sup>
Caliste-64	4 x IDeF-X V1.1	8 x 8	900	10 x 10	1	900	3.0
Caliste-256	8 x IDeF-X V2	16 x 16	580	10 x 10	1	860	8.3
Caliste-HD	8 x IDeF-X HD	16 x 16	625	10 x 10	1	670	2
Caliste-O	8 x IDeF-X HD	16 x 16	800	14 x 14	2	927	1



# D2R1: design changes

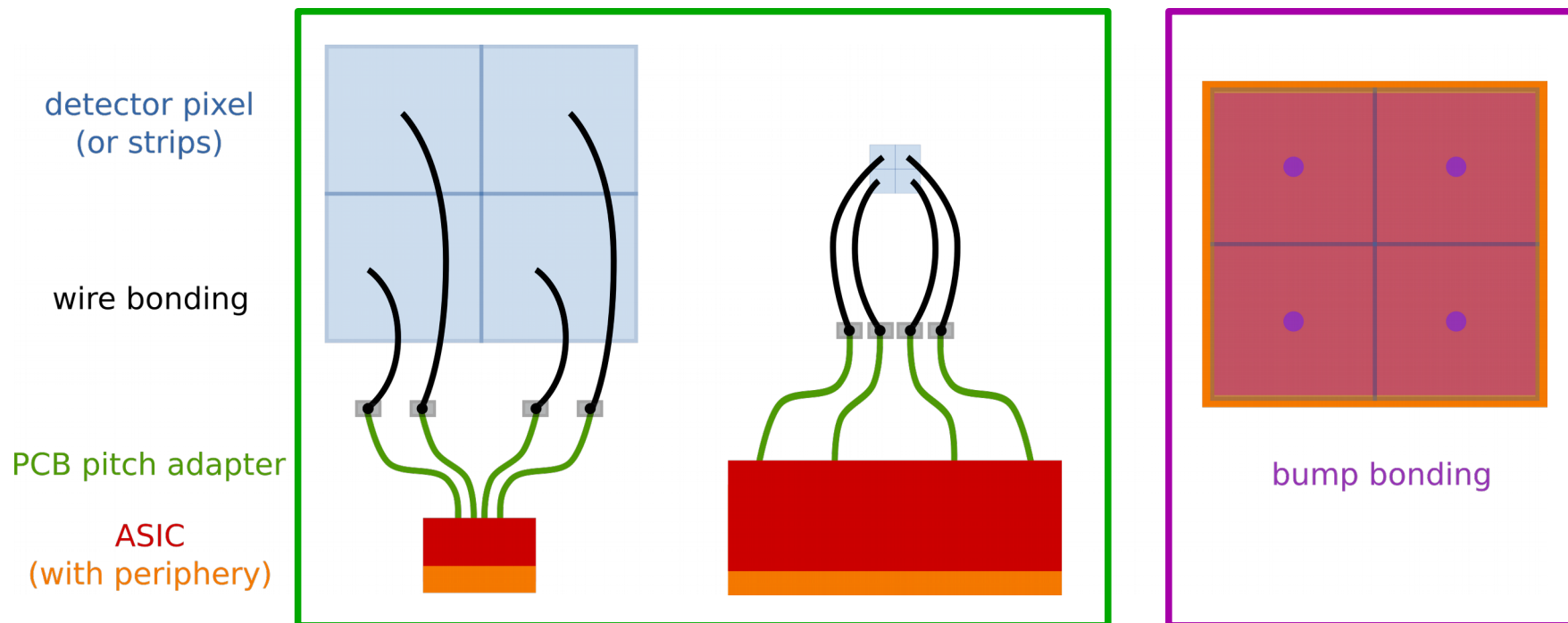
- **What do we want to achieve?**
  - Spectro-imaging detector placed in the focus of a high resolution X-ray optics (10-20'' for a focal length of 10-20m)
- **Which parameters need modification?**
  - pixel pitch → much lower (defined by the mirror resolution and by the constraints for the spectral resolution)
  - power consumption per channel → much lower as there are many channels per area
- **Important parameters to keep:**
  - spectral res. → nearly Fano limited (like for Calsite-HD)
  - dynamic range → 2-250 keV (limited by mirror efficiency)
- **How to do it?**
  - New concept: hybrid detector

# REVIEW: ASIC parameters of interest

	# ch	size	technology	dynamic range	energy range	floor noise	power
	-	um <sup>2</sup>	-	fC	keV (CdTe)	e <sup>-</sup> (rms)	mW/ch
IDeF-X V1.1	16	3000 x 4000	350 nm 3.3 V	10	250	37	2.8
IDeF-X V2	32	2800 x 6400	350 nm 3.3 V	8	200	33	3.0
IDeF-X HD	32	3500 x 5900	350 nm 3.3 V	10-40	250-1000	31	0.8
D2R1	256	<b>16 x 16</b> <b>(300 x 300)</b> + 300 um GR	<b>180 nm</b> <b>1.8 V</b>	10	250	<=31	<b>0.18</b>

# D2R1: a hybrid detector

- how to connect detector and ASIC?
  - **wire bonding**: + (almost) independent of detector or ASIC layout
    - additional stray capacitance
  - **bump bonding**: + minimal stray capacitance
    - ASIC size has to be adapted to detector size



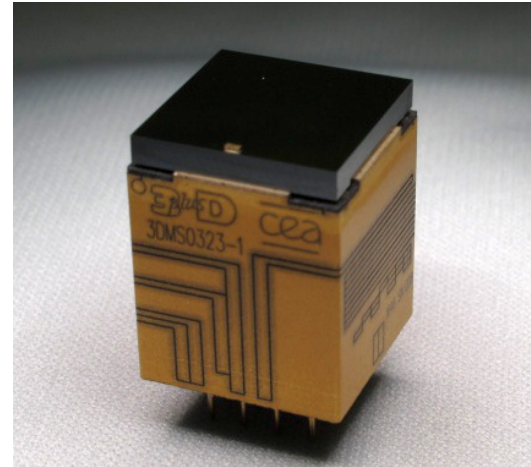
# D2R1: a hybrid detector

Wire bonding connection  
(System in Package)

- 4-side buttability
- stray capacitance

smaller pixels

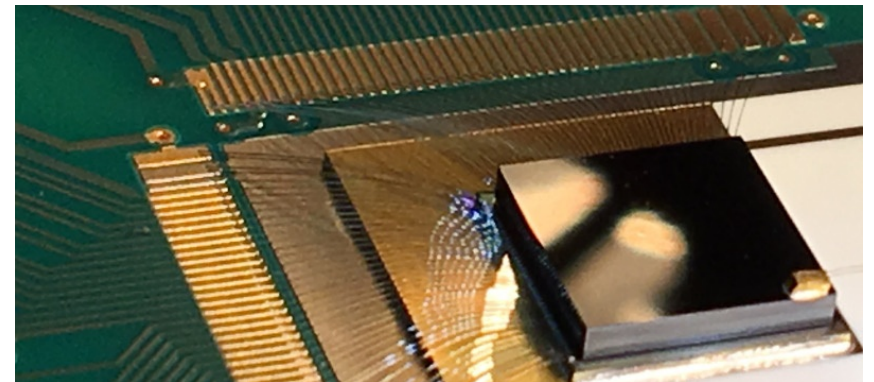
hybrid detector



Caliste-0



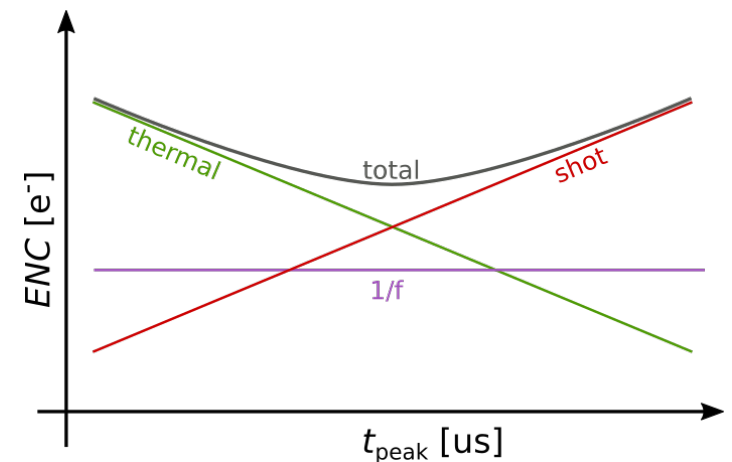
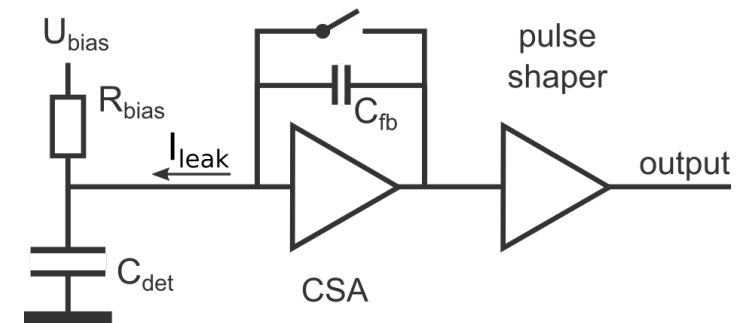
Caliste-256



D2R1

# D2R1: noise analysis in a nutshell

- electronic noise mainly defined by the CSA
- $ENC^2 = ENC_{TH}^2 + ENC_F^2 + ENC_{SH}^2$ 
  - **thermal noise**  $ENC_{TH}^2 = (C_{fb} + C_{in})^2 * a_{TH} / t_{peak}$
  - **1/f noise**  $ENC_F^2 = (C_{fb} + C_{in})^2 * a_F$
  - **shot noise**  $ENC_{SH}^2 = I_{leak} * t_{peak} * a_{SH}$
- detector parameters:
  - input capacitance  $C_{in}$
  - leakage current  $I_{leak}$
- ASIC parameters:  $a_{TH}$ ,  $a_F$ ,  $a_{SH}$ ,  $C_{fb}$ 
  - the a-parameters depend on the shaper and on the CSA input transistor → “Caterpillar” optimization
  - $C_{fb}$  defines the dynamic range
- operational parameters: shaping time  $t_{peak}$



# D2R1: CSA optimization

- electronic noise mainly defined by the CSA

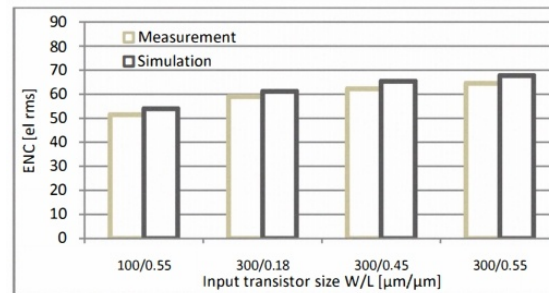
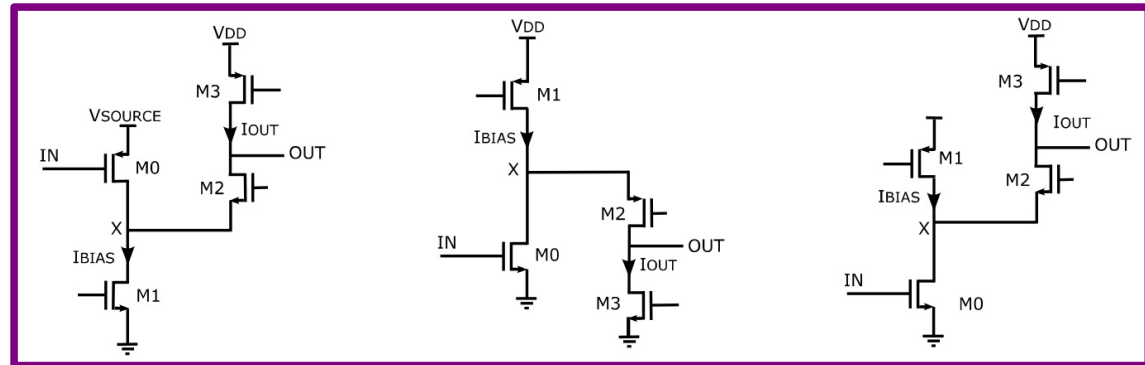
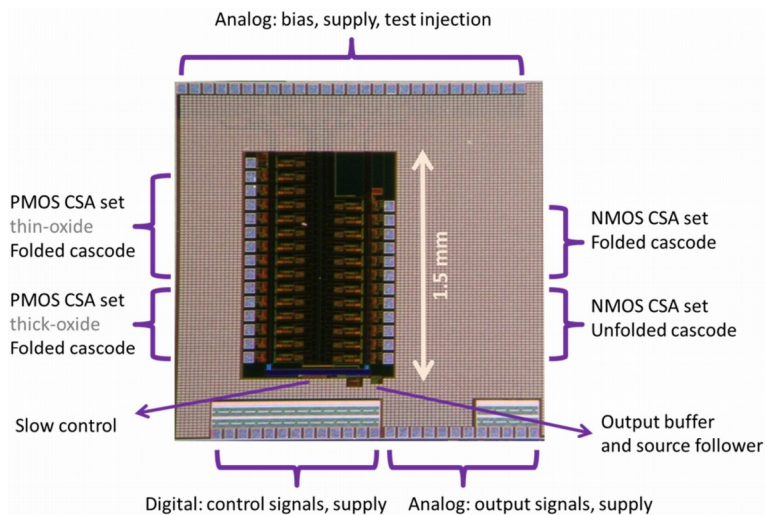
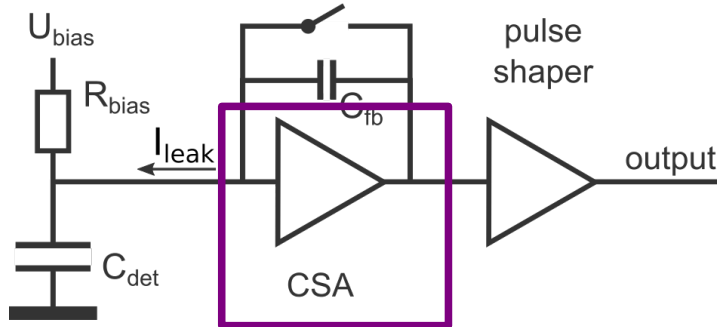


Fig. 16 PMOS thin ox. ENC<sub>MIN</sub> for I<sub>BIAS</sub>=2 μA I<sub>LEAK</sub>=5 pA and C<sub>IN</sub>=0.3 pF

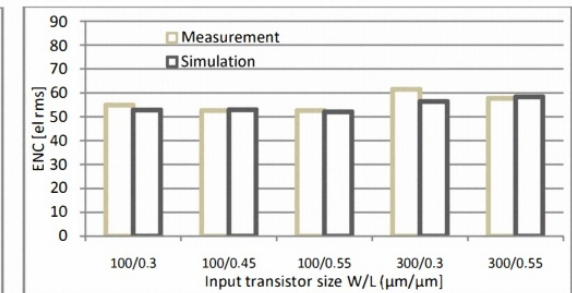


Fig. 19 PMOS thick oxide ENC<sub>MIN</sub> for I<sub>BIAS</sub>=10 μA I<sub>LEAK</sub>=5 pA and C<sub>IN</sub>=1 pF

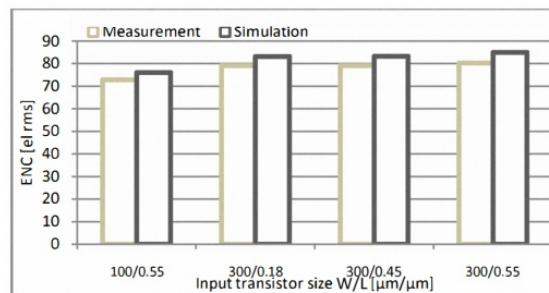


Fig. 17 PMOS thin oxide ENC<sub>MIN</sub> with I<sub>BIAS</sub>=2 μA I<sub>LEAK</sub>=5 pA and C<sub>IN</sub>=1 pF

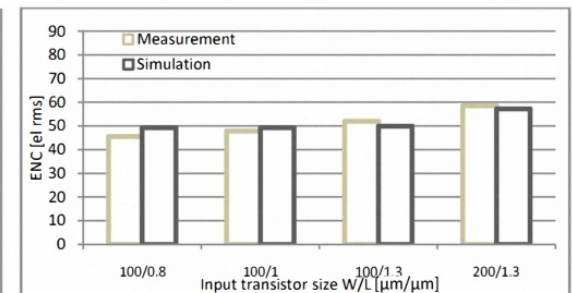
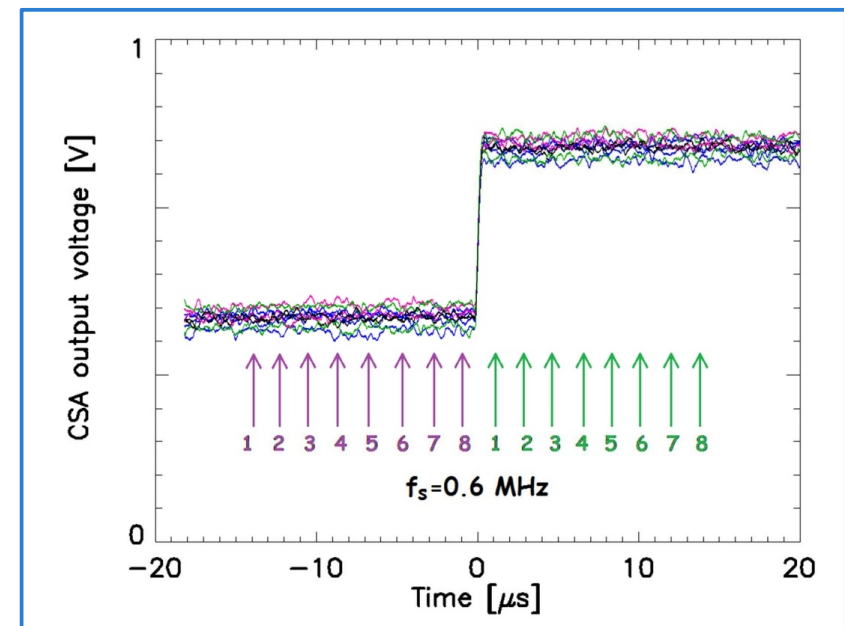
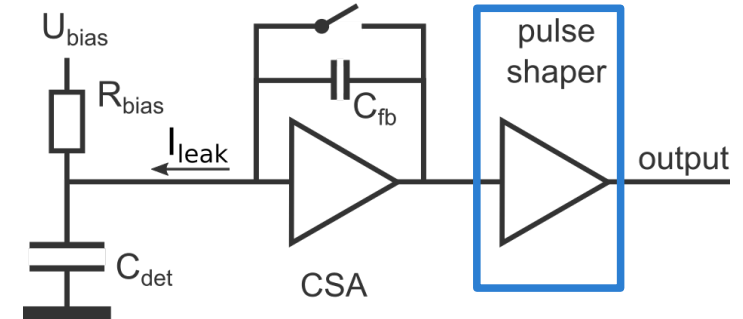


Fig. 20 NMOS thin ox. ENC<sub>MIN</sub> for I<sub>BIAS</sub>=10 μA I<sub>LEAK</sub>=5 pA and C<sub>IN</sub>=0.3 pF

see Michalowska et al., 2011, IEEE, 653-659

# D2R1: filter = pulse shaper

- signal :  $U(t) \xrightarrow{FT}$  signal power (f)
- noise:  $U(t) \xrightarrow{FT}$  noise power (f)
- optimize SNR by attenuating more noise than signal
  - band pass: low-pass + high-pass filter
- within IDeF-X: CR-RC<sup>N</sup> filter (semi-Gaussian)
  - implementation as analog electronics
  - realized as opamp-based active filter
  - $t_{\text{peak}} = N * RC$
- Multi Correlated Double Sampling (MCDS)
  - discrete processing method with sampling rate  $f_s$
  - output = mean(baseline) - mean(baseline + signal)
  - averaging → low-pass filter
  - subtraction → high-pass filter
  - filter parameter can be adjusted easily:  $t_{\text{peak}} = N/f_s$

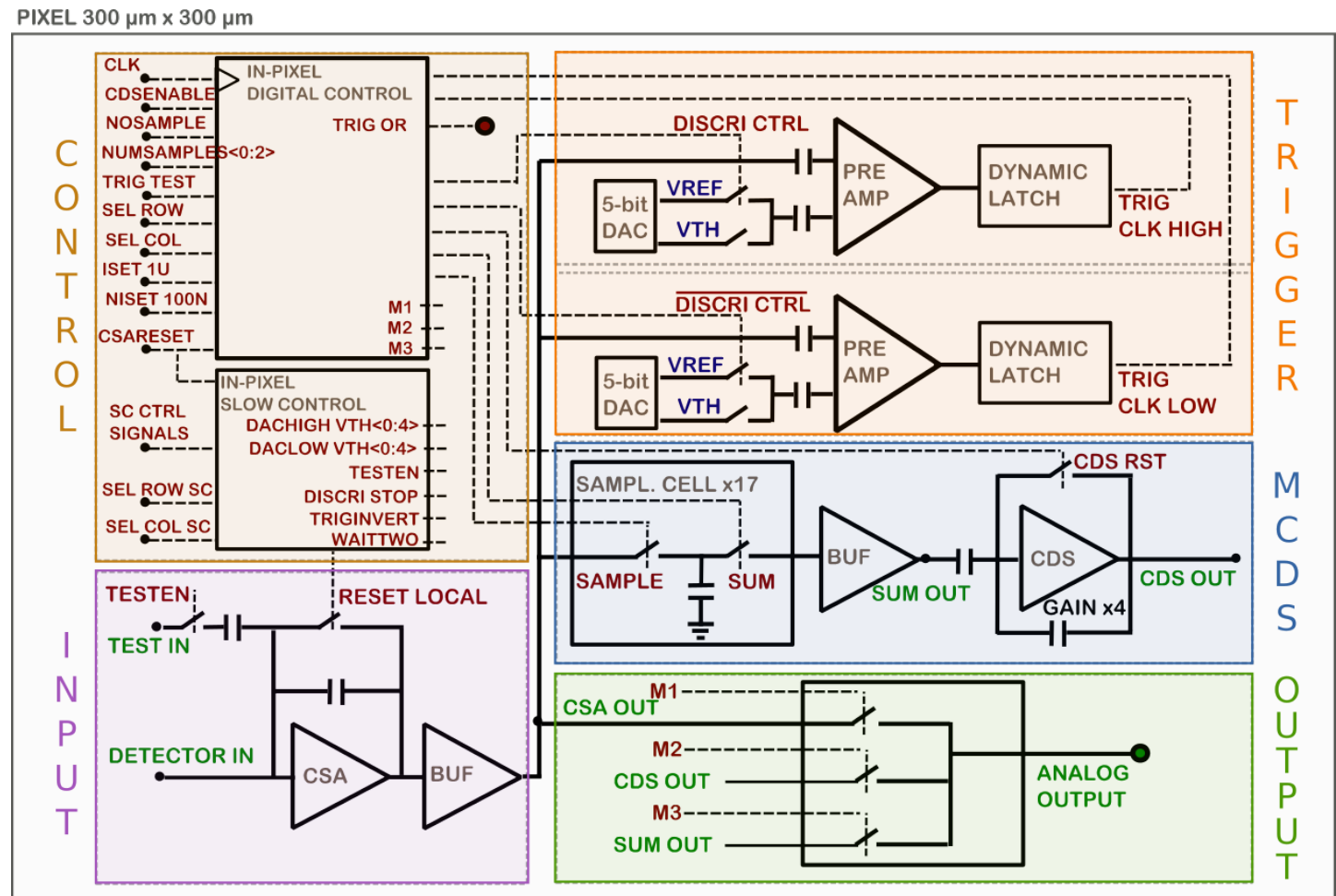


Michalowska, thesis Irfu, 2013

# D2R1: architecture

## - 256 x pixel architecture

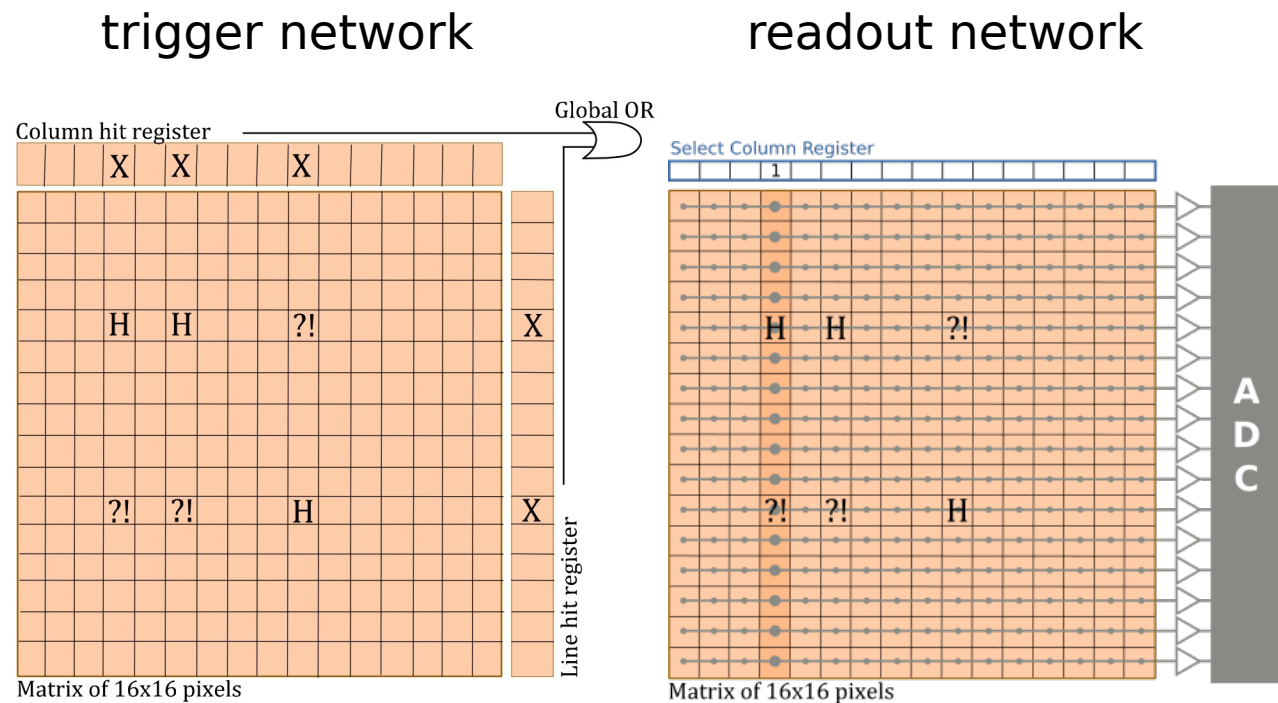
- CSA
- MCDS
- Trigger logic
- control





# D2R1: architecture

- 256 x pixel architecture
  - CSA
  - MCDS
  - Trigger logic
  - control
- **1 x top-level architecture**
  - set in-pixel slow control
  - global trigger
  - addressing column to read



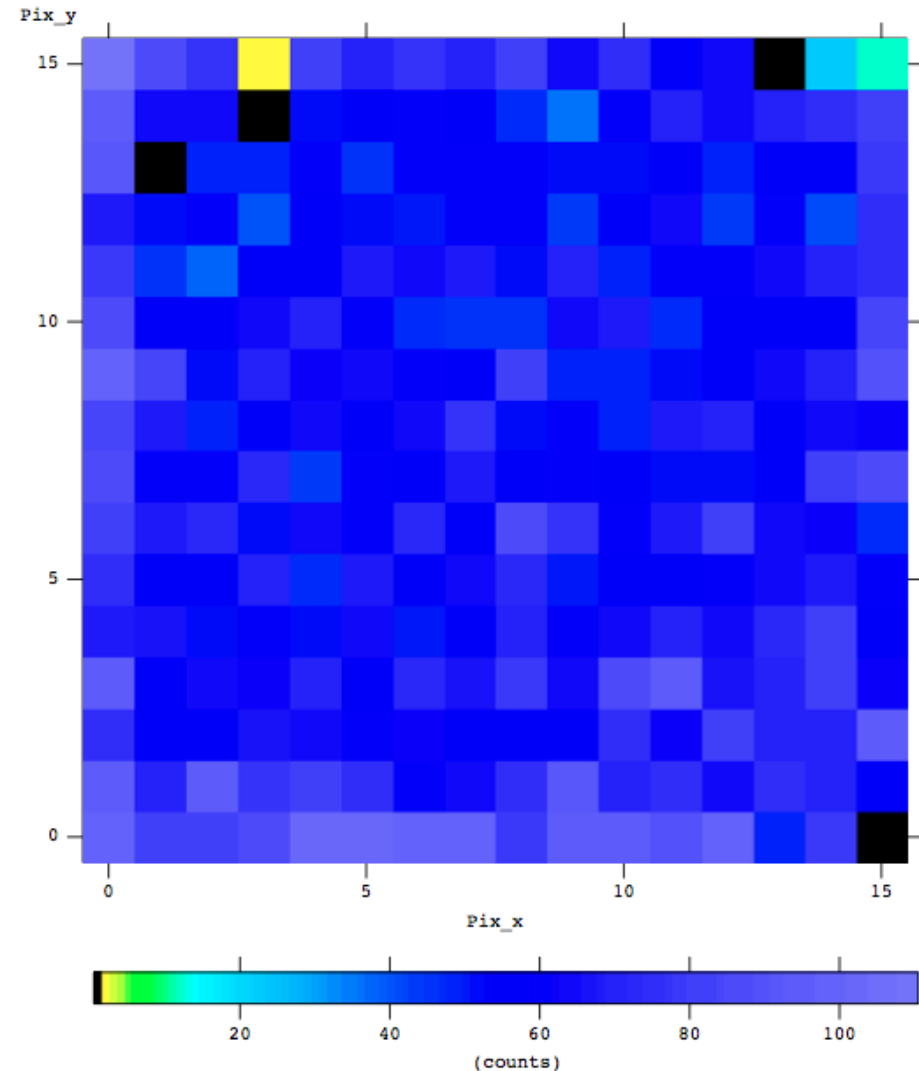
# D2R1: measurements

- cooling down to  $T = -7^{\circ}\text{C}$
- depletion voltage  $U = 300\text{V}$  for  $d = 750\ \mu\text{m}$  detector thickness
- sources:
  - Am-241
  - Co-57



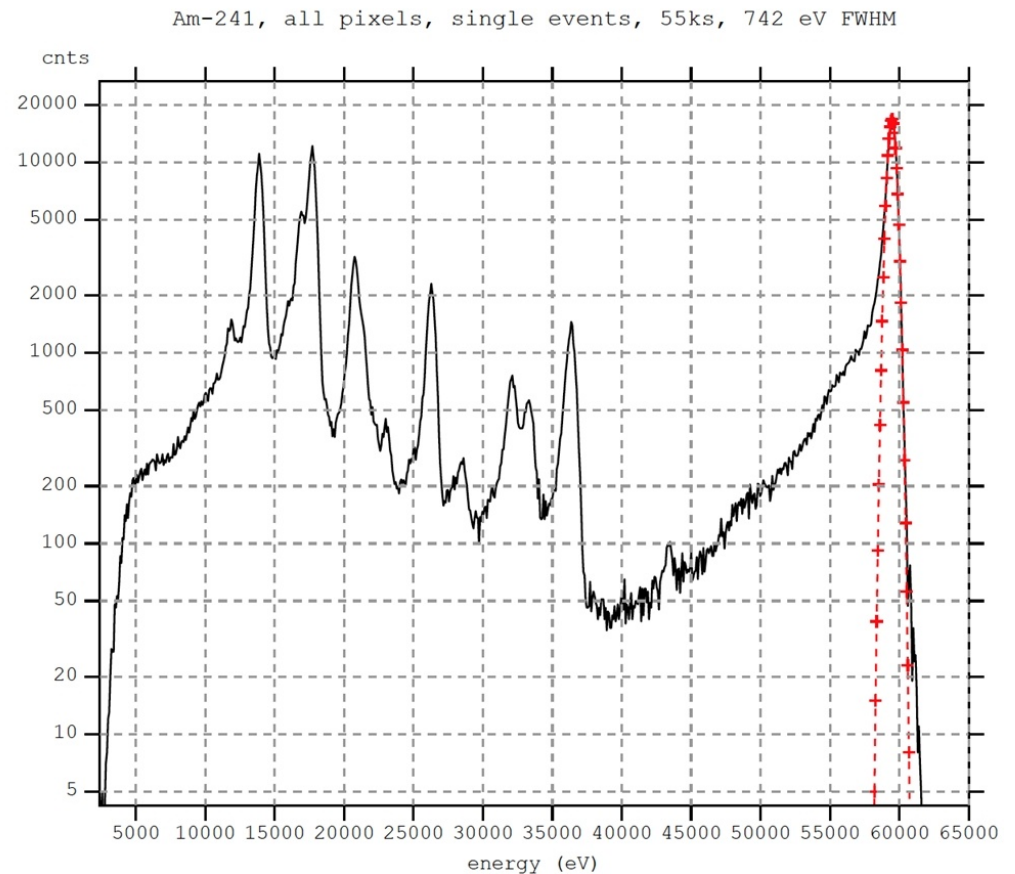
# D2R1: measurements

- cooling down to  $T = -7^{\circ}\text{C}$
- depletion voltage  $U = 300\text{V}$
- sources:
  - Am-241
  - Co-57
- results:
  - (almost) all pixel are working  $\rightarrow$  bump bonding seems fine



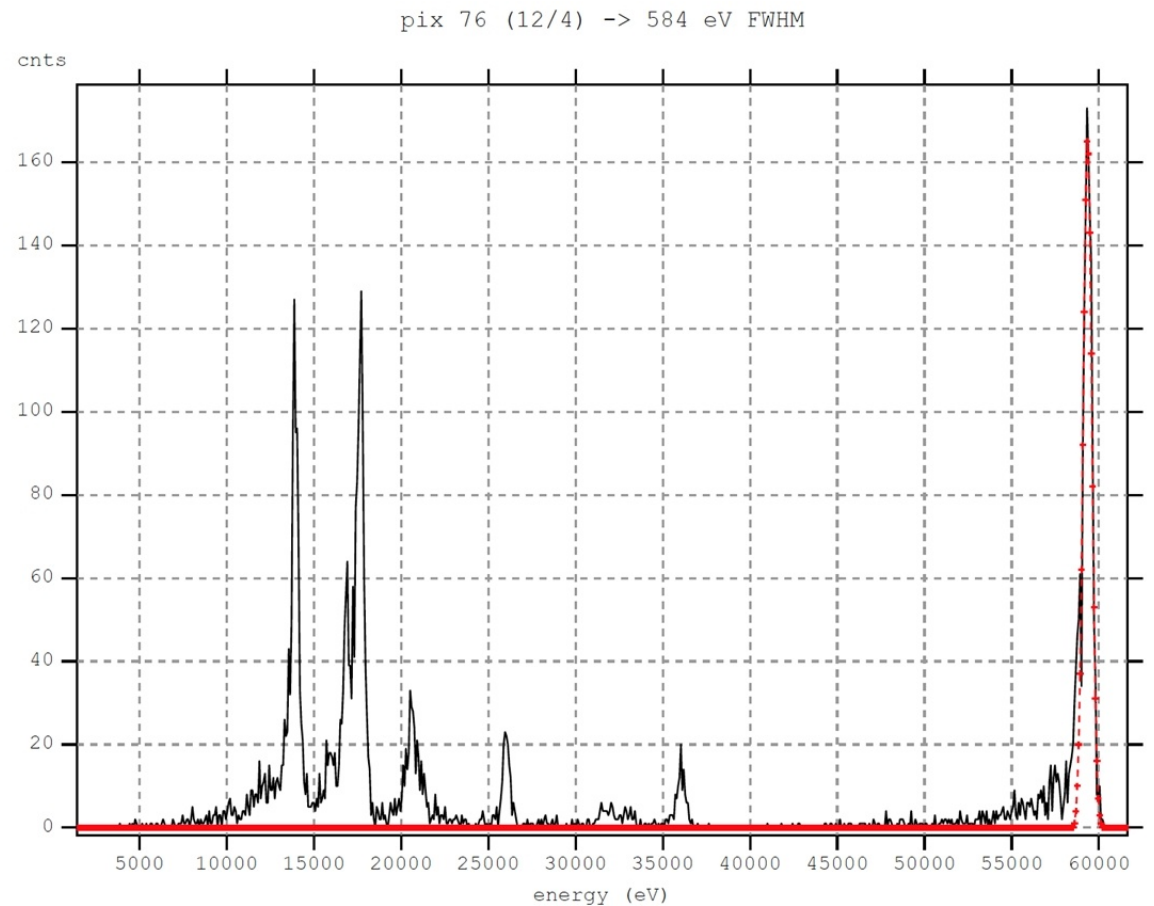
# D2R1: measurements

- cooling down to  $T = -7^\circ\text{C}$
- depletion voltage  $U = 300\text{V}$
- sources:
  - **Am-241**
  - Co-57
- results:
  - (almost) all pixel are working  $\rightarrow$  bump bonding seems fine
  - avg. resolution: 742 eV FWHM @ 60 keV



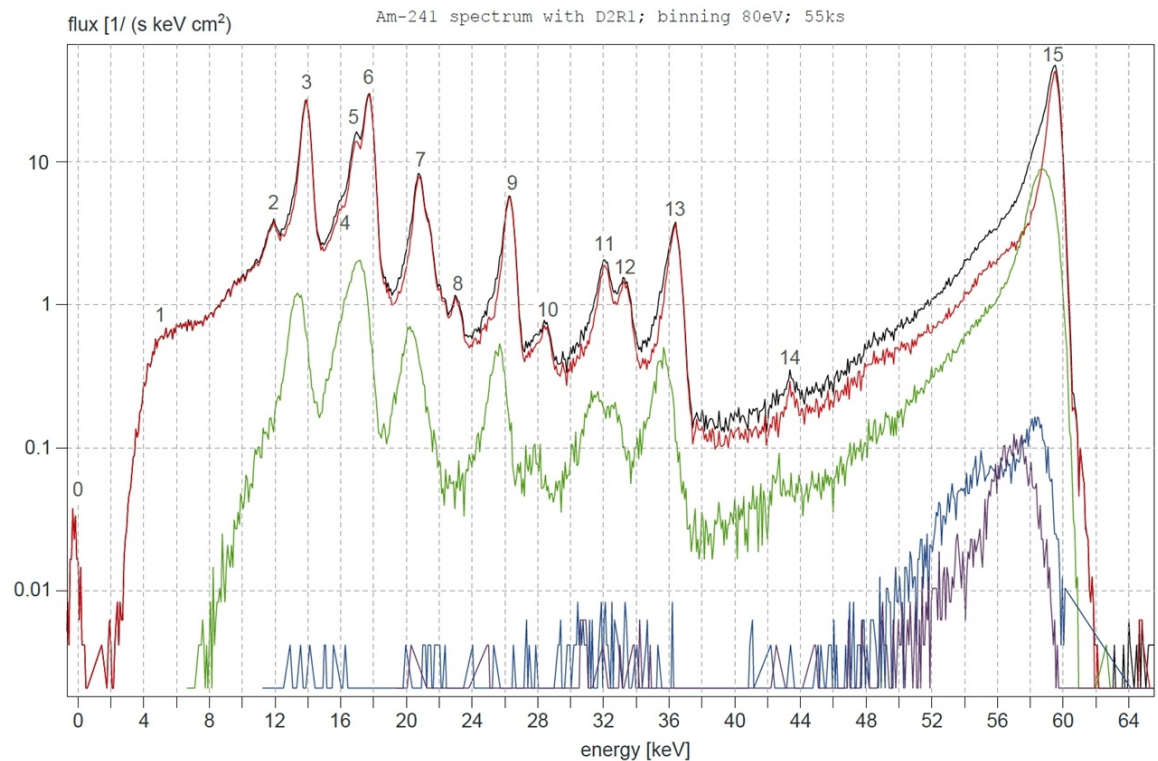
# D2R1: measurements

- cooling down to  $T = -7^\circ\text{C}$
- depletion voltage  $U = 300\text{V}$
- sources:
  - **Am-241**
  - Co-57
- results:
  - (almost) all pixel are working  $\rightarrow$  bump bonding seems fine
  - avg. resolution: 742 eV FWHM @ 60 keV
  - best pixel: 584 eV FWHM @ 60 keV



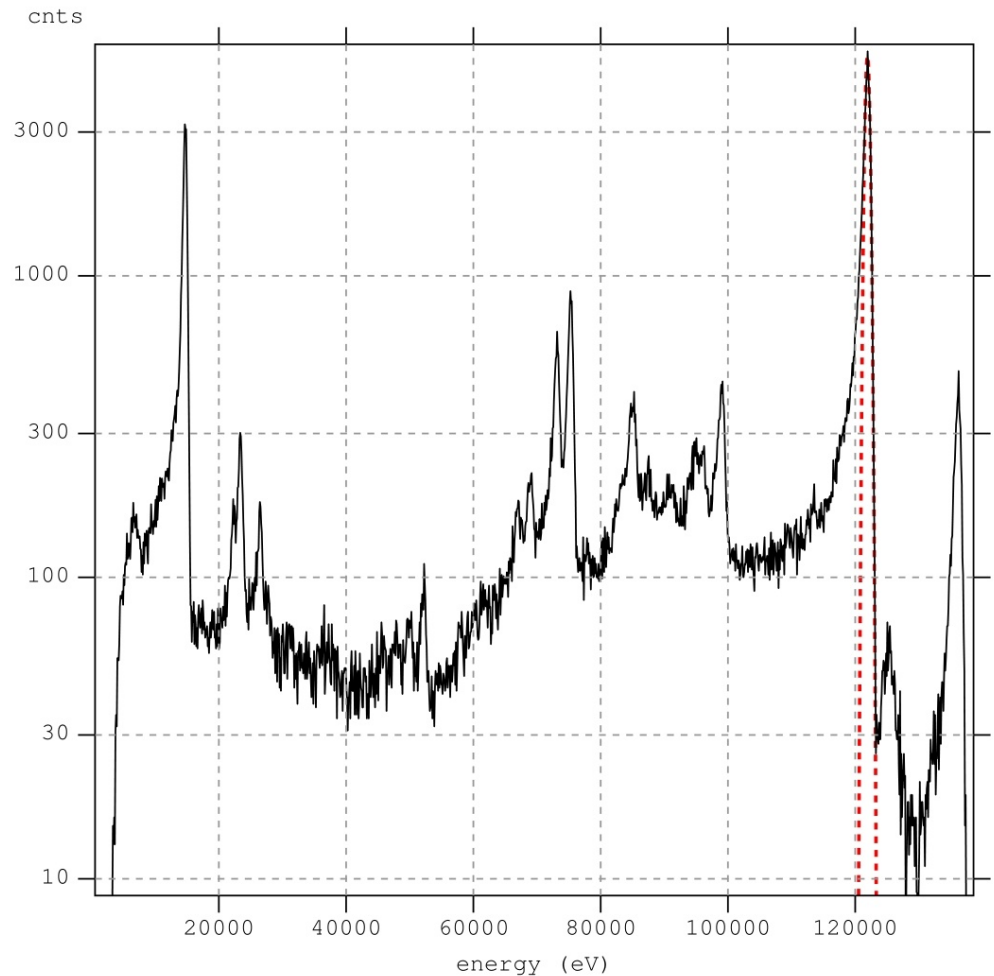
# D2R1: measurements

- cooling down to  $T = -7^\circ\text{C}$
- depletion voltage  $U = 300\text{V}$
- sources:
  - **Am-241**
  - Co-57
- results:
  - (almost) all pixel are working  $\rightarrow$  bump bonding seems fine
  - avg. resolution: 742 eV FWHM @ 60 keV
  - best pixel: 584 eV FWHM @ 60 keV



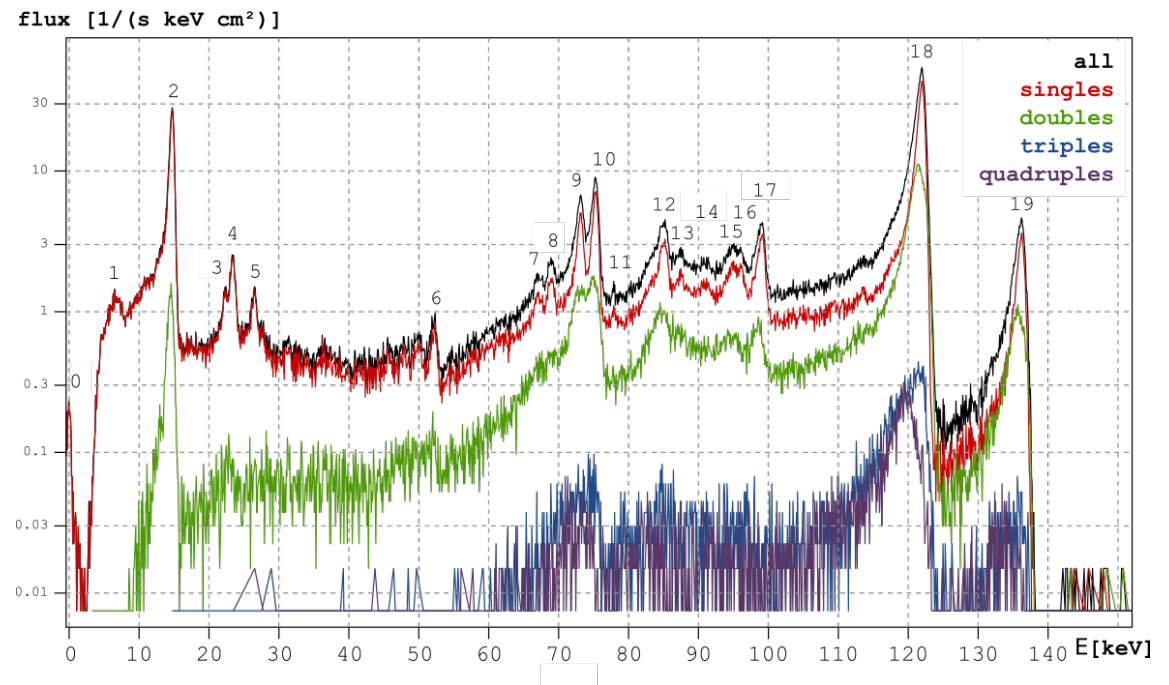
# D2R1: measurements

- cooling down to  $T = -7^\circ\text{C}$
- depletion voltage  $U = 300\text{V}$
- sources:
  - Am-241
  - **Co-57**
- results:
  - (almost) all pixel are working  $\rightarrow$  bump bonding seems fine
  - avg. resolution: 919 eV FWHM @ 122 keV
  - best pixel: 817 eV FWHM @ 122 keV



# D2R1: measurements

- cooling down to  $T = -7^\circ\text{C}$
- depletion voltage  $U = 300\text{V}$
- sources:
  - Am-241
  - **Co-57**
- results:
  - (almost) all pixel are working  $\rightarrow$  bump bonding seems fine
  - avg. resolution: 919 eV FWHM @ 122 keV
  - best pixel: 817 eV FWHM @ 122 keV





# D2R1: next steps

- **Test pixel homogeneity and bump bonding reliability with 4 more D2R1 detector modules**

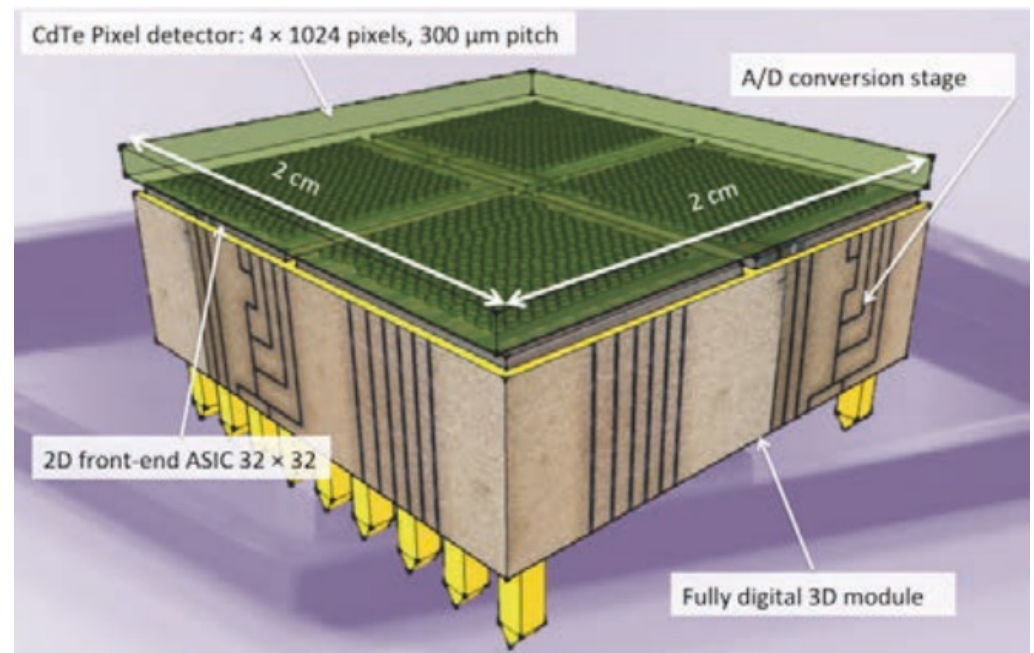
- **Study splits events in more detail:**

- singles	81.2 %	} for Am-241
- doubles	16.5 %	
- triples	0.6 %	
- quadruples	0.7 %	
- mismatches	1.0 %	

- **Investigate the application as X-ray polarimeter**

# OUTLOOK: MC2

- D2R1 → D2R2:
  - 16 x 16 pixels → 32 x 32 pixels
  - 0.5 x 0.5 cm<sup>2</sup> → 1 x 1 cm<sup>2</sup>
- OWB-1: ADC
  - 32 channel 13 bit ADC for space applications
- MC2: 4 x (D2R2 + OWB-1)
  - 64 x 64 pixel
  - 2 x 2 cm<sup>2</sup>
  - fully digital (ADC included)



# OUTLOOK: MC2

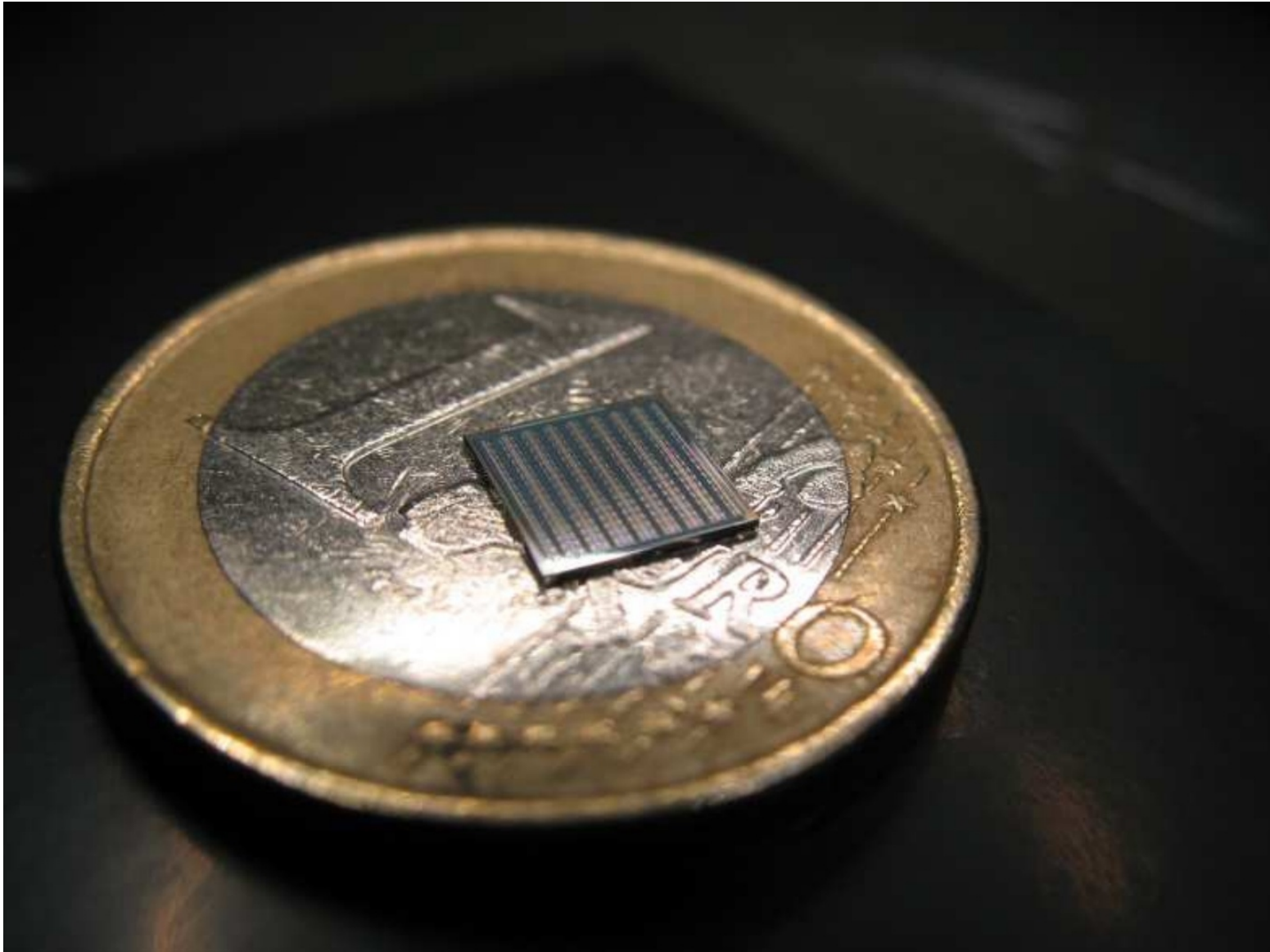
	ASIC	# pix	pixel pitch	detector area	thickness	spectr. res	power
			um	mm <sup>2</sup>	mm	eV (FWHM @ 60 keV)	mW/mm <sup>2</sup>
Caliste-64	4 x IDeF-X V1.1	8 x 8	900	10 x 10	1	900	3.0
Caliste-256	8 x IDeF-X V2	16 x 16	580	10 x 10	1	860	8.3
Caliste-HD	8 x IDeF-X HD	16 x 16	625	10 x 10	1	670	2
Caliste-O	8 x IDeF-X HD	16 x 16	800	14 x 14	2	927	1
Caliste-MC2	4 x D2R2	64 x 64	300	20 x 20	0.75 – 2.0	at least like Caliste-HD	2

## References:

- A. Michalowska et al., 2011, “Multi-dimensional optimization of charge preamplifier in 0.18 um CMOS technology, IEEE
- A. Michalowska, 2013, “Studies and development of a readout ASIC for pixelated CdTe detectors for space applications”, Ph. D. dissertation, Université Paris Sud – Paris XI, Saclay, France
- F. Bouyjou et al., 2017, “A 32-Channel 13-b ADC for Space Applications”

**Thanks for your  
attention !**

# D2R1



# D2R1: trigger

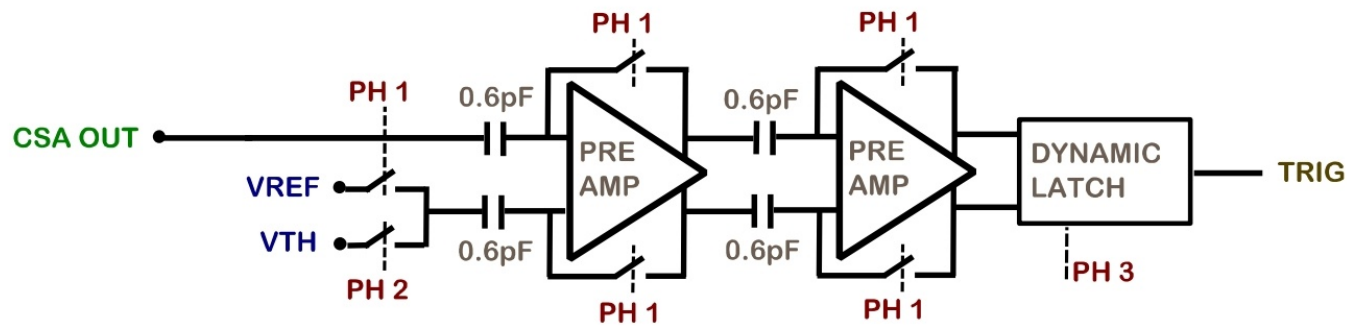


Figure 4.6 Block diagram of a single discriminator in the  $D^2R_1$  readout channel. Each channel contains two identical discriminators, operating with interleaved clock phases.

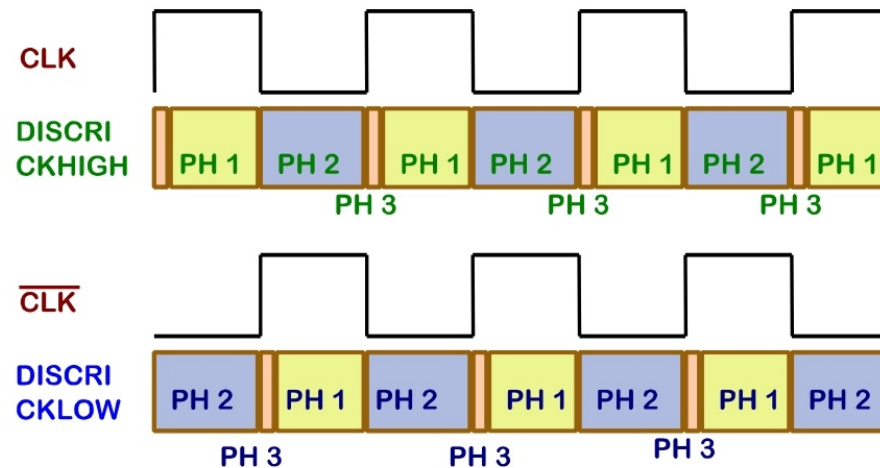


Figure 4.7 Chronogram of control phases of two parallel discriminators of  $D^2R_1$  readout channel. One supervised by the  $CLK$  signal and one by the  $\overline{CLK}$  signal.